

Amendments to the Claims

Kindly cancel claims 1-14, and add new claims 15-21 as set forth below. In accordance with current amendment practice, all pending claims are reproduced below. Changes in the amended claims are shown by underlining (for added matter) and strikethrough/double brackets (for deleted matter).

1-14. Canceled.

15. (New) A semiconductor processing method comprising:

providing a first conductive material above a substrate, with a first contact hole being disposed adjacent to the first conductive material, wherein a horizontal surface of the first conductive material is adjacent to the first contact hole;

providing a mask extending over a portion of the first conductive material, the mask having a second contact hole formed therein, the second contact hole extending over the first contact hole and exposing a portion of the horizontal surface of the first conductive material;

disposing a second conductive material in the first contact hole; and

providing an electrically insulating spacer lining at least a portion of the second contact hole and extending to the second conductive material, wherein the insulating spacer has a dimension sufficient so that first conductive material is unexposed, and wherein the second conductive material is recessed below the horizontal surface.

16. (New) The method of claim 15, further comprising providing a spacer along a sidewall of the first contact hole to isolate the second conductive material from the first conductive material along the sidewall, wherein the second conductive material is borderless to the first conductive material.

17. (New) The method of claim 15, wherein the first conductive material comprises a cap-free gate conductor of a field effect transistor.

18. (New) The method of claim 15, further comprising providing a bit-line contact disposed so that it is partially in the second contact hole, and electrically connecting to the second conductive material in the first contact hole, and extending at least partially above the first conductive material.

19. (New) The method of claim 18, wherein the first conductive material comprises a cap-free gate of the field effect transistor.

20. (New) The method of claim 19, wherein the cap-free gate comprises a memory word-line, and is borderless to the conductor and the bit-line contact.

21. (New) The method of claim 15, wherein the providing of the electrically insulating spacer includes creating an insulating layer aligned to the second contact hole and extending into the first conductive material and the second conductive material.

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